

| FORM PTO-1449 | | | | Atty. Docket No. XA-9689A | | Appln. No. 10/616355 | |
|--|----|--|---------|---------------------------------------|-------|-------------------------|-------------|
| LIST OF DOCUMENTS CITED BY APPLICANT | | | | Applicant Norikatsu TAKAURA et al. | | | |
| | | | | Filing Date Herewith 7/10/03 | | Group 2813 | |
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| Examiner Initial | | Document Number | Date | Name | Class | Sub-class | Filing Date |
| <i>JMS</i> | AA | 6,153,490 | 11-2000 | Xing et al. | 438 | 396 | — |
| | AB | | | | | | |
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| | AD | | | | | | |
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| Examiner Initial | | Document Number | Date | Country | Class | Sub-class | Translation |
| <i>JMS</i> | AL | 2000-174225 | 6/00 | Japan | | | Abstract |
| <i>JMS</i> | AM | 09-036318A | 02/97 | Japan | | | |
| <i>JMS</i> | AN | 04-058556A | 02/92 | Japan | | | |
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| OTHER (including author, title, date, pertinent pages, etc.) | | | | | | | |
| <i>JMS</i> | AT | Kistler, N. et al., "Symmetric CMOS in Fully-Depleted Silicon-On-Insulator Using P+-Polycrystalline Si-Ge Gate Electrodes," Dec. 1993, IEDM 93, pp. 727-730. | | | | | |
| Examiner <i>[Signature]</i> | | | | Date Considered 11/12/04 | | | |
| EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant. | | | | | | | |